

SPICE Model Parameters

Please copy this code from the SPICE model into LTSPICE (version 4) software for simulation of the GB20SHT12-CAL.

```
*      MODEL OF GeneSiC Semiconductor Inc.
*
*      $Revision:   1.0           $
*      $Date:      05-SEP-2013   $
*
*      GeneSiC Semiconductor Inc.
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*      Dulles, VA 20166
*
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*
*      These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
*      OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
*      TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
*      PARTICULAR PURPOSE."
*      Models accurate up to 2 times rated drain current.
*
*      Start of GB20SHT12-CAL SPICE Model
*
.SUBCKT GB20SHT12 ANODE KATHODE
D1 ANODE KATHODE GB20SHT12_25C; Call the Schottky Diode Model
D2 ANODE KATHODE GB20SHT12_PIN; Call the PiN Diode Model
. MODEL GB20SHT12_25C D
+ IS      1.74E-13      RS      0.05105
+ TRS1    0.005        TRS2    1.68E-5
+ N       1.2637323    IKF     1.884319
+ EG      1.2          XTI     3
+ CJO     1.15E-09    VJ     0.44
+ M       1.5          FC      0.5
+ TT      1.00E-10    BV     1200
+ IBV     1.00E-03    VPK    1200
+ IAVE    20          TYPE    SiC_Schottky
+ MFG     GeneSiC_Semiconductor
. MODEL GB20SHT12_PIN D
+ IS      5.15E-15     RS      0.2
+ N       3.1605       IKF     0.00055844
+ EG      3.23         XTI     3
+ FC      0.5         TT      0
+ BV      1200        IBV     1.00E-03
+ VPK     1200        IAVE    20
+ TYPE    SiC_PiN
.ENDS
*
*      End of GB20SHT12-CAL SPICE Model
```